

Features

- Advanced SGT MOS Technology
- 100% EAS Guaranteed
- Green Device Available
- Low $R_{DS(on)}$
- Super Low Gate Charge
- ESD Protected

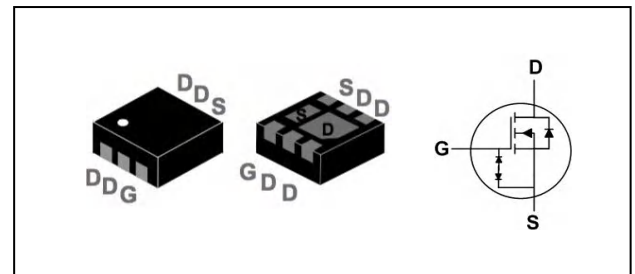
Product Summary

V_{DS}	100	V
$R_{DS(ON), Typ}$	39	m Ω
I_D	6	A

Applications

- Portable Equipment.
- Battery Powered Systems.
- Hard Switching and High-Speed Circuit.

DFN2*2-6L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	6	A
$I_D @ T_A = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	4.5	A
I_{DM}	Pulsed Drain Current ²	18	A
I_{AS}	Avalanche Current	3.6	A
$P_D @ T_A = 25^\circ\text{C}$	Total Power Dissipation ⁴	3.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	120	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =2A	---	39	48	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	2.0	3.0	4.0	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =80V, V _{GS} =0V, T _J =55°C	---	---	10	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±10	uA
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.7	---	Ω
Q _g	Total Gate Charge	V _{DS} =50V, V _{GS} =10V, I _D =3A	---	6.6	---	nC
Q _{gs}	Gate-Source Charge		---	1.8	---	
Q _{gd}	Gate-Drain Charge		---	2.1	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =50V, V _{GS} =10V, R _G =3.3Ω I _D =3A	---	6	---	ns
T _r	Rise Time		---	23	---	
T _{d(off)}	Turn-Off Delay Time		---	9	---	
T _f	Fall Time		---	19	---	
C _{iss}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=1MHz	---	336	---	pF
C _{oss}	Output Capacitance		---	82	---	
C _{rss}	Reverse Transfer Capacitance		---	5	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	6	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =3A, di/dt=100A/μs, T _J =25°C	---	30	---	nS
Q _{rr}	Reverse Recovery Charge		---	30	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V, V_{GS}=10V, L=0.1mH, I_{AS}=3.6A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

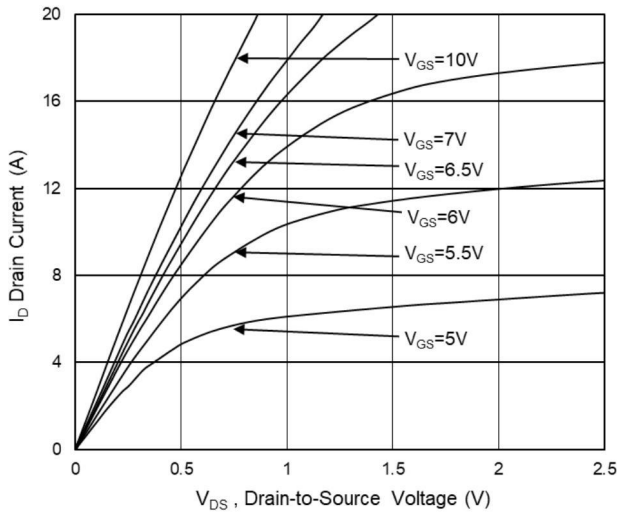


Fig.1 Typical Output Characteristics

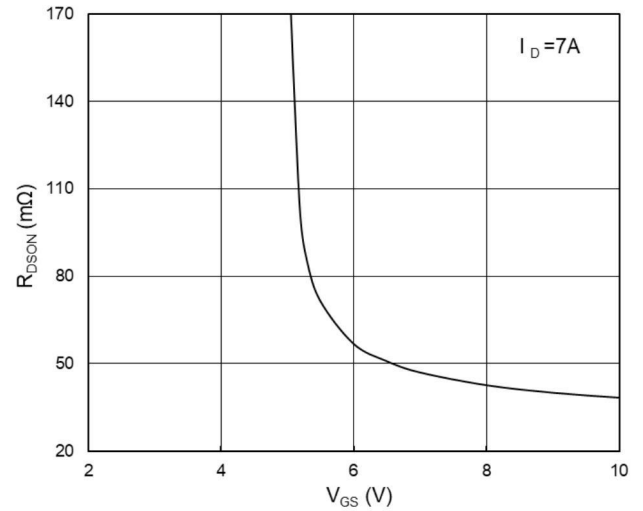


Fig.2 On-Resistance vs. G-S Voltage

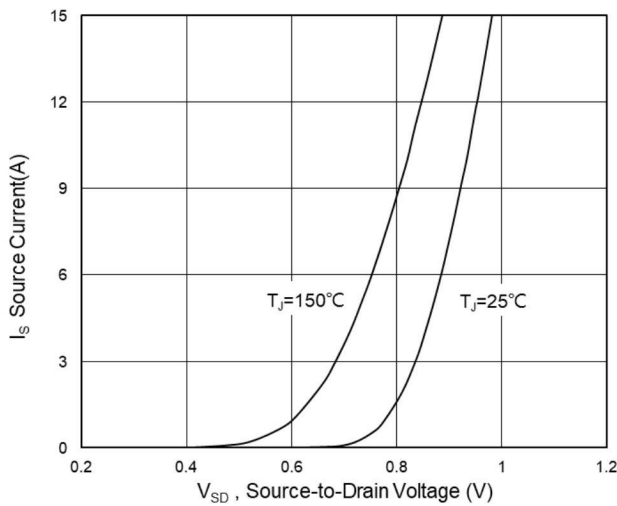


Fig.3 Source Drain Forward Characteristics

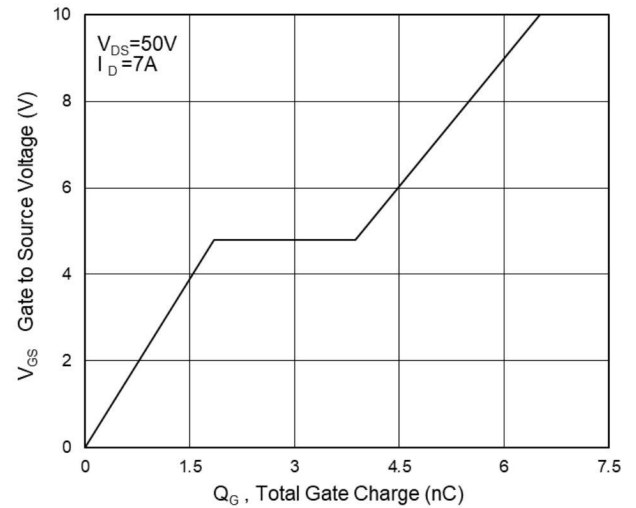


Fig.4 Gate-Charge Characteristics

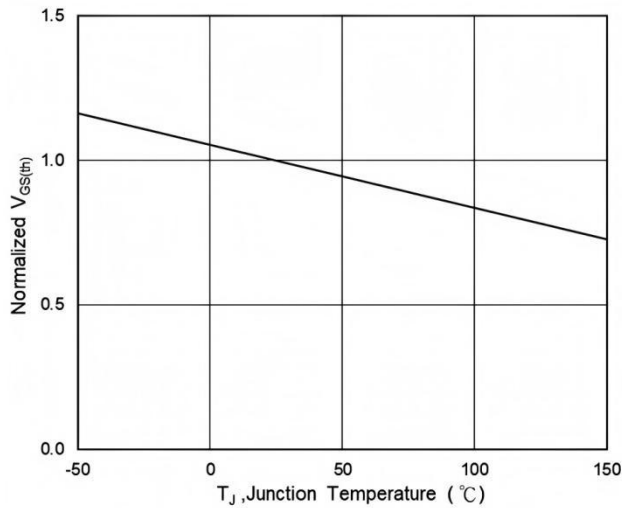


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

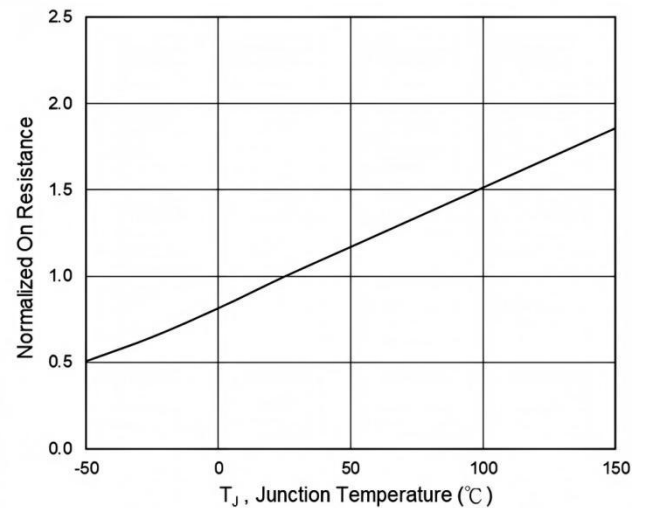


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

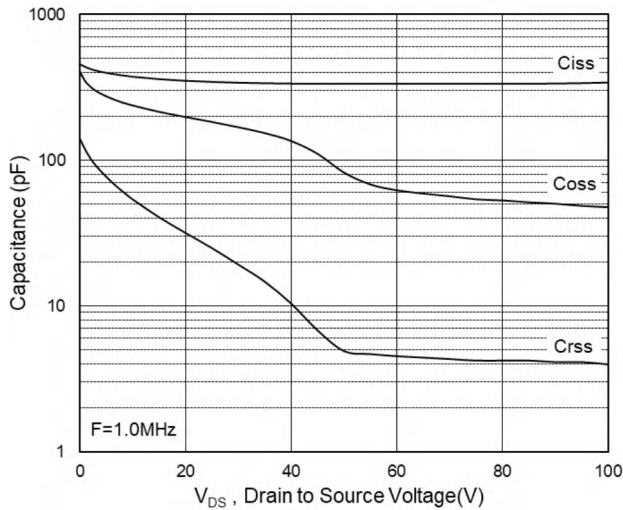


Fig.7 Capacitance

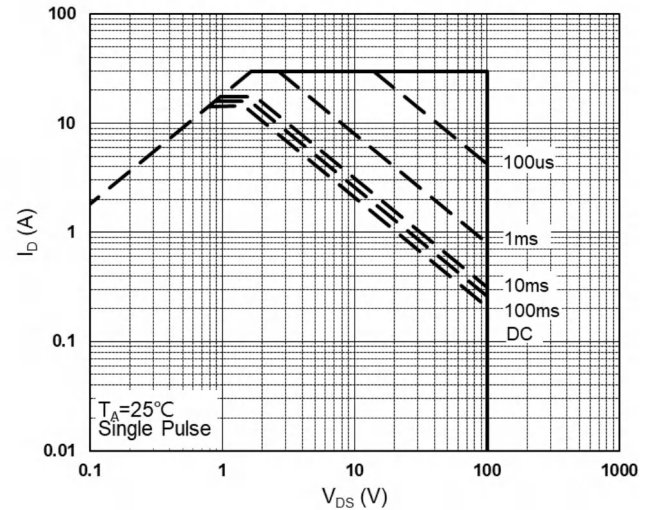


Fig.8 Safe Operating Area

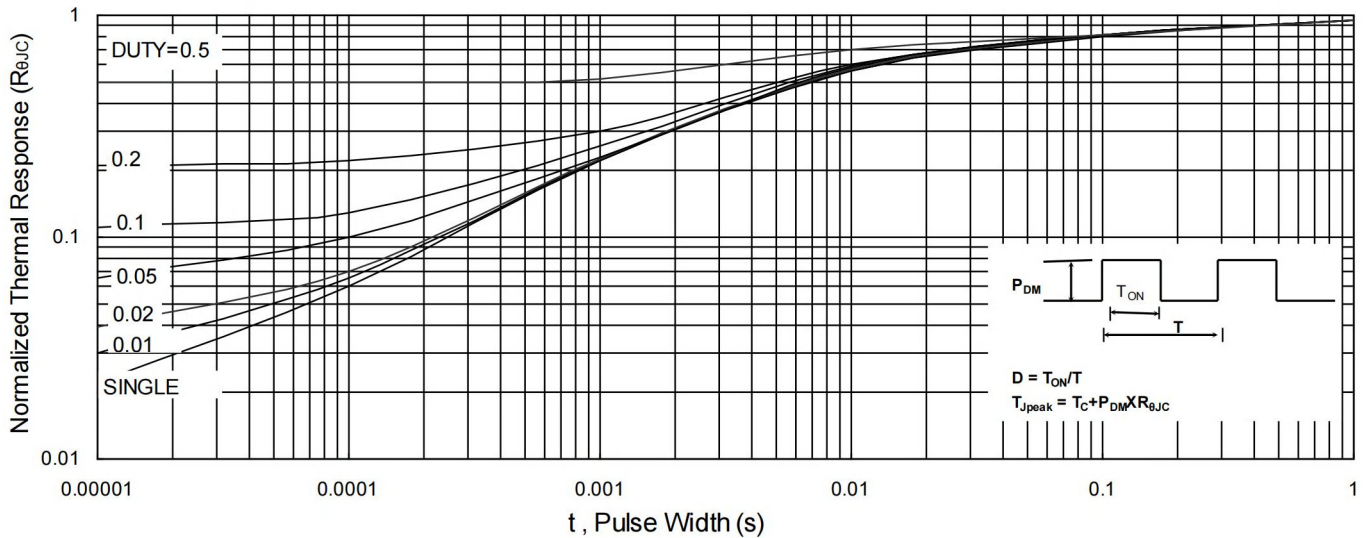


Fig.9 Normalized Maximum Transient Thermal Impedance

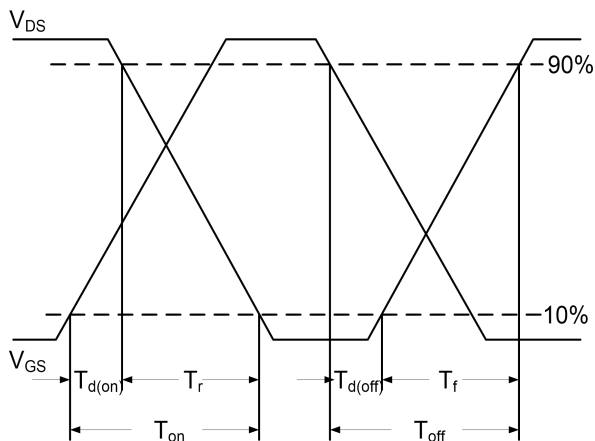


Fig.10 Switching Time Waveform

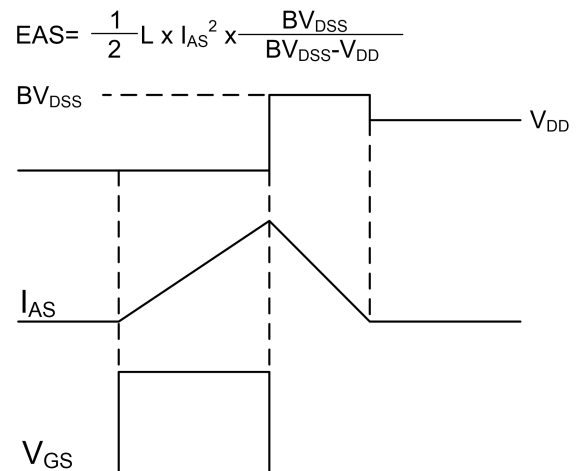
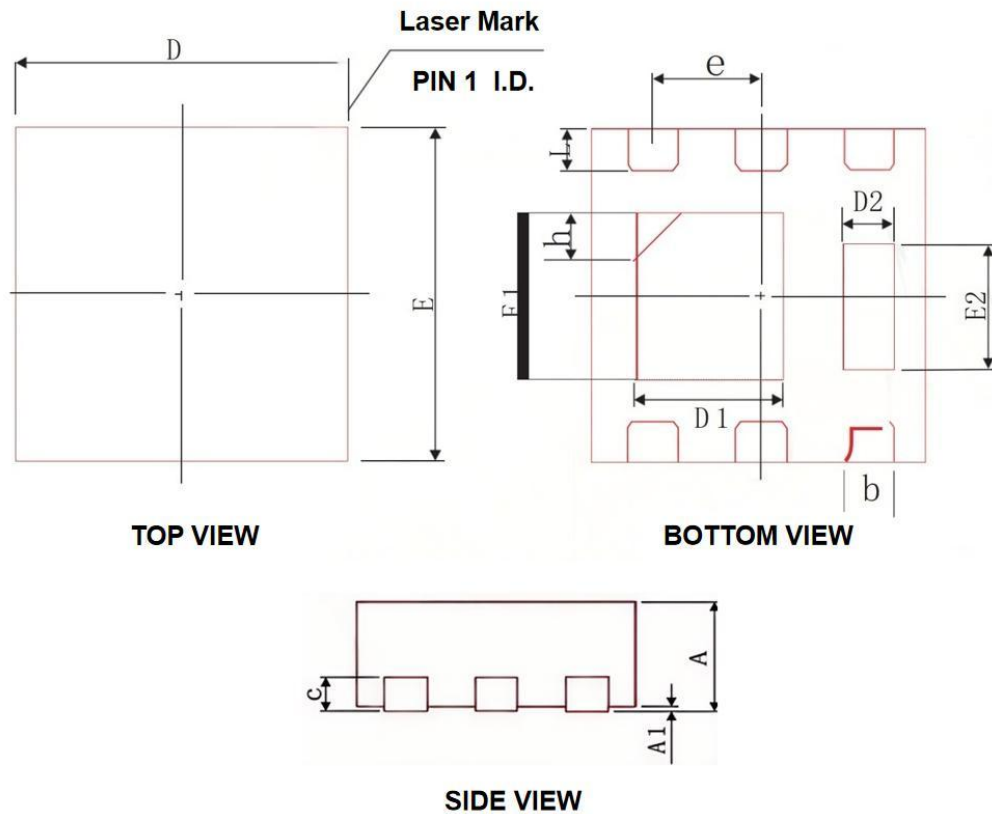


Fig.11 Unclamped Inductive Switching Waveform

Ordering Information

Part Number	Package code	Packaging
HSCB0010E	DFN2*2-6L	3000/Tape&Reel

DFN2*2-6L 2EP Package Outline



COMMON DIMENSIONS (UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	0.70	0.75	0.80
A1	0.00	0.02	0.05
b	0.20	0.25	0.30
D	1.95	2.00	2.07
E	1.95	2.00	2.07
D1	0.80	0.90	1.00
E1	0.90	1.00	1.10
D2	0.20	0.30	0.40
E2	0.65	0.75	0.85
L	0.20	0.25	0.35
h	0.20	0.25	0.30
C	0.203 REF		
e	0.65 BSC		

HSCB0010E Marking:

